Jean-Michel Gerard

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Photoluminescence of Single InAs Quantum Dots Obtained by Self-Organized Growth on GaAs. Physical Review Letters, 1994, 73, 716-719.	7.8	1,053
2	Enhanced Spontaneous Emission by Quantum Boxes in a Monolithic Optical Microcavity. Physical Review Letters, 1998, 81, 1110-1113.	7.8	946
3	Exciton-Photon Strong-Coupling Regime for a Single Quantum Dot Embedded in a Microcavity. Physical Review Letters, 2005, 95, 067401.	7.8	665
4	A highly efficient single-photon source based on a quantum dot in a photonic nanowire. Nature Photonics, 2010, 4, 174-177.	31.4	519
5	Single-mode solid-state single photon source based on isolated quantum dots in pillar microcavities. Applied Physics Letters, 2001, 79, 2865-2867.	3.3	472
6	Spin Relaxation Quenching in Semiconductor Quantum Dots. Physical Review Letters, 2001, 86, 1634-1637.	7.8	385
7	Strong-coupling regime for quantum boxes in pillar microcavities: Theory. Physical Review B, 1999, 60, 13276-13279.	3.2	374
8	Strong Purcell effect for InAs quantum boxes in three-dimensional solid-state microcavities. Journal of Lightwave Technology, 1999, 17, 2089-2095.	4.6	355
9	Strong Electron-Phonon Coupling Regime in Quantum Dots: Evidence for Everlasting Resonant Polarons. Physical Review Letters, 1999, 83, 4152-4155.	7.8	347
10	A highly efficient single-photon source based on a quantum dot in a photonic nanowire. Nature Photonics, 0, , .	31.4	331
11	Quantum Cascade of Photons in Semiconductor Quantum Dots. Physical Review Letters, 2001, 87, .	7.8	289
12	Quantum boxes as active probes for photonic microstructures: The pillar microcavity case. Applied Physics Letters, 1996, 69, 449-451.	3.3	263
13	High-Q wet-etched GaAs microdisks containing InAs quantum boxes. Applied Physics Letters, 1999, 75, 1908-1910.	3.3	240
14	Optically Driven Spin Memory inn-Doped InAs-GaAs Quantum Dots. Physical Review Letters, 2002, 89, 207401.	7.8	234
15	Strain-mediated coupling in a quantum dot–mechanical oscillator hybrid system. Nature Nanotechnology, 2014, 9, 106-110.	31.5	224
16	Solid-state single photon sources: the nanowire antenna. Optics Express, 2009, 17, 2095.	3.4	214
17	Inhibition, Enhancement, and Control of Spontaneous Emission in Photonic Nanowires. Physical Review Letters, 2011, 106, 103601.	7.8	194
18	Unconventional motional narrowing in the optical spectrum of a semiconductor quantum dot. Nature Physics, 2006, 2, 759-764.	16.7	190

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19	Giant optical nonlinearity induced by a single two-level system interacting with a cavity in the Purcell regime. Physical Review A, 2007, 75, .	2.5	173
20	InAs quantum boxes: Highly efficient radiative traps for light emitting devices on Si. Applied Physics Letters, 1996, 68, 3123-3125.	3.3	155
21	Intraband absorption in n-doped InAs/GaAs quantum dots. Applied Physics Letters, 1997, 71, 2785-2787.	3.3	142
22	Third-harmonic generation in InAs/GaAs self-assembled quantum dots. Physical Review B, 1999, 59, 9830-9833.	3.2	140
23	Electrically driven high-Q quantum dot-micropillar cavities. Applied Physics Letters, 2008, 92, .	3.3	135
24	Strongly coupling a cavity to inhomogeneous ensembles of emitters: Potential for long-lived solid-state quantum memories. Physical Review A, 2011, 84, .	2.5	130
25	Acoustic phonon sidebands in the emission line of single InAs/GaAs quantum dots. Physical Review B, 2003, 68, .	3.2	127
26	Dielectric GaAs Antenna Ensuring an Efficient Broadband Coupling between an InAs Quantum Dot and a Gaussian Optical Beam. Physical Review Letters, 2013, 110, 177402.	7.8	125
27	Optical investigation of the self-organized growth of InAs/GaAs quantum boxes. Journal of Crystal Growth, 1995, 150, 351-356.	1.5	123
28	Long Polaron Lifetime in InAs/GaAs Self-Assembled Quantum Dots. Physical Review Letters, 2002, 88, 177402.	7.8	119
29	Solid-state single photon sources: light collection strategies. European Physical Journal D, 2002, 18, 197-210.	1.3	112
30	Controlling the dynamics of a coupled atom-cavity system by pure dephasing. Physical Review B, 2010, 81, .	3.2	112
31	Monolayer-scale optical investigation of segregation effects in semiconductor heterostructures. Physical Review B, 1992, 45, 6313-6316.	3.2	103
32	Imaging the Wave-Function Amplitudes in Cleaved Semiconductor Quantum Boxes. Physical Review Letters, 2000, 85, 1068-1071.	7.8	102
33	Pure emitter dephasing: A resource for advanced solid-state single-photon sources. Physical Review A, 2009, 79, .	2.5	102
34	Near-surface GaAs/Ga0.7Al0.3As quantum wells: Interaction with the surface states. Physical Review B, 1990, 41, 12945-12948.	3.2	99
35	Infrared spectroscopy of intraband transitions in self-organized InAs/GaAs quantum dots. Journal of Applied Physics, 1997, 82, 3396-3401.	2.5	99
36	In situprobing at the growth temperature of the surface composition of (InGa)As and (InAl)As. Applied Physics Letters, 1992, 61, 2096-2098.	3.3	96

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37	Photoluminescence Up-Conversion in Single Self-AssembledInAs/GaAsQuantum Dots. Physical Review Letters, 2001, 87, 207401.	7.8	95
38	Scanning tunneling microscopy and scanning tunneling spectroscopy of self-assembled InAs quantum dots. Applied Physics Letters, 1998, 73, 96-98.	3.3	90
39	Solid-State Cavity-Quantum Electrodynamics with Self-Assembled Quantum Dots. Topics in Applied Physics, 0, , 269-314.	0.8	88
40	Surface segregation in Ill–V alloys. Journal of Crystal Growth, 1991, 111, 141-150.	1.5	87
41	InAs quantum dots: artificial atoms for solid-state cavity-quantum electrodynamics. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 9, 131-139.	2.7	86
42	Optical study of GaAs/AlAs pillar microcavities with elliptical cross section. Applied Physics Letters, 1998, 72, 1421-1423.	3.3	85
43	Controlling the emission profile of a nanowire with a conical taper. Optics Letters, 2008, 33, 1693.	3.3	85
44	In-plane polarized intraband absorption in InAs/GaAs self-assembled quantum dots. Physical Review B, 1998, 58, 10562-10567.	3.2	83
45	Experimental probing of quantum-well eigenstates. Physical Review Letters, 1989, 62, 2172-2175.	7.8	82
46	Far-infrared magnetospectroscopy of polaron states in self-assembled InAs/GaAs quantum dots. Physical Review B, 2002, 65, .	3.2	79
47	Midinfrared absorption and photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2001, 78, 2327-2329.	3.3	78
48	Interferometric correlation spectroscopy in single quantum dots. Applied Physics Letters, 2002, 81, 2737-2739.	3.3	78
49	Line narrowing in single semiconductor quantum dots: Toward the control of environment effects. Physical Review B, 2002, 66, .	3.2	78
50	High quality ultrathin InAs/GaAs quantum wells grown by standard and lowâ€ŧemperature modulatedâ€fluxes molecular beam epitaxy. Applied Physics Letters, 1988, 53, 568-570.	3.3	75
51	Infrared second-order optical susceptibility in InAs/GaAs self-assembled quantum dots. Physical Review B, 2000, 61, 5562-5570.	3.2	74
52	Single artificial atoms in silicon emitting at telecom wavelengths. Nature Electronics, 2020, 3, 738-743.	26.0	72
53	Vertically aligned graphene nanosheets on silicon using an ionic liquid electrolyte: towards high performance on-chip micro-supercapacitors. Journal of Materials Chemistry A, 2015, 3, 19254-19262.	10.3	71
54	Temperature dependence of the zero-phonon linewidth in quantum dots: An effect of the fluctuating environment. Physical Review B, 2007, 75, .	3.2	68

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55	Cavity-Funneled Generation of Indistinguishable Single Photons from Strongly Dissipative Quantum Emitters. Physical Review Letters, 2015, 114, 193601.	7.8	68
56	Phonon sidebands in exciton and biexciton emission from single GaAs quantum dots. Physical Review B, 2004, 69, .	3.2	65
57	Polarization of the interband optical dipole in InAs/GaAs self-organized quantum dots. Physical Review B, 2001, 63, .	3.2	63
58	Dynamical equilibrium between excitons and free carriers in quantum wells. Solid State Communications, 1995, 95, 287-293.	1.9	60
59	Single photon emission from individual GaAs quantum dots. Applied Physics Letters, 2003, 82, 2206-2208.	3.3	59
60	Probing exciton localization in nonpolarGaNâ^•AlNquantum dots by single-dot optical spectroscopy. Physical Review B, 2007, 75, .	3.2	59
61	Analysis of the Filling Pattern Dependence of the Photonic Bandgap for Two-dimensional Systems. Journal of Modern Optics, 1994, 41, 295-310.	1.3	57
62	Influence of AlN overgrowth on structural properties of GaN quantum wells and quantum dots grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2004, 96, 1104-1110.	2.5	57
63	Second-harmonic generation resonant withs-ptransition in InAs/GaAs self-assembled quantum dots. Physical Review B, 2001, 63, .	3.2	56
64	Electromagnetic study of the quality factor of pillar microcavities in the small diameter limit. Applied Physics Letters, 2004, 84, 4726-4728.	3.3	56
65	Simulation of waveguiding and emitting properties of semiconductor nanowires with hexagonal or circular sections. Journal of the Optical Society of America B: Optical Physics, 2009, 26, 2396.	2.1	55
66	Designs for high-efficiency electrically pumped photonic nanowire single-photon sources. Optics Express, 2010, 18, 21204.	3.4	54
67	A fiber-coupled quantum-dot on a photonic tip. Applied Physics Letters, 2016, 108, .	3.3	54
68	Optical losses in plasma-etched AlGaAs microresonators using reflection spectroscopy. Applied Physics Letters, 1999, 74, 911-913.	3.3	53
69	Temperature dependence of intersublevel absorption in InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2002, 80, 4620-4622.	3.3	51
70	Efficient photonic mirrors for semiconductor nanowires. Optics Letters, 2008, 33, 2635.	3.3	51
71	Saturation of intraband absorption and electron relaxation time in n-doped InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 1998, 73, 3818-3821.	3.3	48
72	Dynamical ultrafast all-optical switching of planar GaAsâ^•AlAs photonic microcavities. Applied Physics Letters, 2007, 91, .	3.3	48

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73	Ultimate fast optical switching of a planar microcavity in the telecom wavelength range. Applied Physics Letters, 2011, 98, 161114.	3.3	48
74	Broad Diversity of Near-Infrared Single-Photon Emitters in Silicon. Physical Review Letters, 2021, 126, 083602.	7.8	48
75	Spontaneous emission spectrum of a two-level atom in a very-high- <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Q</mml:mi>cavity. Physical Review A, 2008, 77, .</mml:math 	2.5	47
76	Structural and optical properties of high quality InAs/GaAs shortâ€period superlattices grown by migrationâ€enhanced epitaxy. Applied Physics Letters, 1989, 54, 30-32.	3.3	46
77	Time-resolved probing of the Purcell effect for InAs quantum boxes in GaAs microdisks. Applied Physics Letters, 2001, 78, 2828-2830.	3.3	45
78	Evidence for low density of nonradiative defects in ZnO nanowires grown by metal organic vapor-phase epitaxy. Applied Physics Letters, 2007, 91, 143120.	3.3	45
79	Linearly Polarized, Single-Mode Spontaneous Emission in a Photonic Nanowire. Physical Review Letters, 2012, 108, 077405.	7.8	45
80	Optical properties of some III–V strained-layer superlattices. Superlattices and Microstructures, 1989, 5, 51-58.	3.1	44
81	Fast exciton spin relaxation in single quantum dots. Physical Review B, 2005, 71, .	3.2	44
82	Correlated photon emission from a single II–VI quantum dot. Applied Physics Letters, 2004, 85, 6251-6253.	3.3	43
83	Design of broadband high-efficiency superconducting-nanowire single photon detectors. Superconductor Science and Technology, 2016, 29, 065016.	3.5	43
84	Strong-coupling regime in pillar semiconductor microcavities. Superlattices and Microstructures, 1997, 22, 371-374.	3.1	42
85	Room temperature, continuous wave lasing in microcylinder and microring quantum dot laser diodes. Applied Physics Letters, 2012, 100, .	3.3	41
86	A single-mode solid-state source of single photons based on isolated quantum dots in a micropillar. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 418-422.	2.7	40
87	Quantum box size effect on vertical self-alignment studied using cross-sectional scanning tunneling microscopy. Applied Physics Letters, 1999, 74, 2608-2610.	3.3	39
88	Continuous-wave versus time-resolved measurements of Purcell factors for quantum dots in semiconductor microcavities. Physical Review B, 2009, 80, .	3.2	39
89	Resonant driving of a single photon emitter embedded in a mechanical oscillator. Nature Communications, 2017, 8, 76.	12.8	39
90	Photonic bandgap of two-dimensional dielectric crystals. Solid-State Electronics, 1994, 37, 1341-1344.	1.4	38

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91	Efficient acoustic phonon broadening in single self-assembled InAs/GaAs quantum dots. Physical Review B, 2001, 65, .	3.2	38
92	Growth and characterization of AlGaInAs lattice matched to InP grown by molecularâ€beam epitaxy. Journal of Applied Physics, 1988, 63, 400-403.	2.5	37
93	Study of isolated cubic GaN quantum dots by low-temperature cathodoluminescence. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 203-206.	2.7	37
94	Exciton spin manipulation inInAsâ^•GaAsquantum dots: Exchange interaction and magnetic field effects. Physical Review B, 2005, 71, .	3.2	37
95	Numerical and Experimental Study of the \$Q\$ Factor of High-\$Q\$ Micropillar Cavities. IEEE Journal of Quantum Electronics, 2010, 46, 1470-1483.	1.9	37
96	Giant optical anisotropy in a single InAs quantum dot in a very dilute quantum-dot ensemble. Applied Physics Letters, 2005, 86, 041904.	3.3	36
97	Quantum communication with quantum dot spins. Physical Review B, 2007, 75, .	3.2	36
98	Optical anisotropy and light extraction efficiency of MBE grown GaN nanowires epilayers. Optics Express, 2011, 19, 527.	3.4	36
99	Harnessing Light with Photonic Nanowires: Fundamentals and Applications to Quantum Optics. ChemPhysChem, 2013, 14, 2393-2402.	2.1	36
100	Highly directive and Gaussian far-field emission from "giant―photonic trumpets. Applied Physics Letters, 2015, 107, .	3.3	36
101	Whispering gallery mode lasing in high quality GaAs/AlAs pillar microcavities. Applied Physics Letters, 2010, 96, 071103.	3.3	34
102	All-optical switching of a microcavity repeated at terahertz rates. Optics Letters, 2013, 38, 374.	3.3	33
103	Tensorial phase control in nonlinear meta-optics. Optica, 2021, 8, 269.	9.3	33
104	High Q whispering gallery modes in GaAs/AlAs pillar microcavities. Optics Express, 2007, 15, 17291.	3.4	31
105	Midinfrared second-harmonic generation in p-type InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 1999, 75, 835-837.	3.3	30
106	Integrated terahertz source based on three-wave mixing of whispering-gallery modes. Optics Letters, 2008, 33, 2416.	3.3	30
107	quantum boxes obtained by self-organized growth: Intrinsic electronic properties and applications. Solid-State Electronics, 1996, 40, 807-814.	1.4	29
108	Purcell effect for CdSeâ^•ZnSe quantum dots placed into hybrid micropillars. Applied Physics Letters, 2005, 87, 233114.	3.3	29

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109	Detection of Single W-Centers in Silicon. ACS Photonics, 2022, 9, 2337-2345.	6.6	29
110	Photoluminescence experiment on quantum dots embedded in a large Purcell-factor microcavity. Physical Review B, 2008, 78, .	3.2	28
111	Structural study of InAs quantum boxes grown by molecular beam epitaxy on a (001) GaAs-on-Si substrate. Applied Physics Letters, 1997, 70, 2398-2400.	3.3	26
112	Bimodal distribution of Indium composition in arrays of low-pressure metalorganic-vapor-phase-epitaxy grown InGaAs/GaAs quantum dots. Applied Physics Letters, 2001, 79, 2157-2159.	3.3	25
113	Energy transfer through laterally confined Bragg mirrors and its impact on pillar microcavities. IEEE Journal of Quantum Electronics, 2005, 41, 1323-1329.	1.9	25
114	Inducing micromechanical motion by optical excitation of a single quantum dot. Nature Nanotechnology, 2021, 16, 283-287.	31.5	25
115	High resolution in situ measurement of the surface composition of InxGa1-xAs and InxAl1-xAs at growth temperature. Journal of Crystal Growth, 1993, 127, 981-985.	1.5	24
116	Nano-fabrication with focused ion beams. Microelectronic Engineering, 2001, 57-58, 865-875.	2.4	24
117	Linear and dynamical photoinduced dichroisms ofInAsâ^•GaAsself-assembled quantum dots: Population relaxation and decoherence measurements. Physical Review B, 2006, 73, .	3.2	24
118	Quantum dot spontaneous emission control in a ridge waveguide. Applied Physics Letters, 2015, 106, .	3.3	24
119	A broadband tapered nanocavity for efficient nonclassical light emission. Optics Express, 2016, 24, 20904.	3.4	24
120	Strong and weak coupling regime in pillar semiconductor microcavities. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 915-919.	2.7	23
121	Novel prospects for self-assembled InAs/GaAs quantum boxes. Journal of Crystal Growth, 1999, 201-202, 1109-1116.	1.5	23
122	Unveiling the ionic exchange mechanisms in vertically-oriented graphene nanosheet supercapacitor electrodes with electrochemical quartz crystal microbalance and ac-electrogravimetry. Electrochemistry Communications, 2018, 93, 5-9.	4.7	22
123	Direct probing of type-II band configurations in semiconductor superlattices. Physical Review B, 1989, 40, 6450-6453.	3.2	21
124	Chapter 3 Optical Studies of Strained III-V Heterolayers. Semiconductors and Semimetals, 1990, , 55-118.	0.7	21
125	Efficient tuning of the carrier capture efficiency of quantum wells by introducing a barrier asymmetry. Applied Physics Letters, 1993, 63, 240-242.	3.3	21
126	Optical characterization and selective addressing of the resonant modes of a micropillar cavity with a white light beam. Physical Review B, 2010, 82, .	3.2	21

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127	Optimal irreversible stimulated emission. New Journal of Physics, 2012, 14, 083029.	2.9	21
128	Strain-Gradient Position Mapping of Semiconductor Quantum Dots. Physical Review Letters, 2017, 118, 117401.	7.8	21
129	Monolayer scale study of segregation effects in InAs/GaAs heterostructures. Journal of Crystal Growth, 1993, 127, 536-540.	1.5	20
130	Growth of InGaAs/GaAs quantum wells with perfectly abrupt interfaces by molecular beam epitaxy. Applied Physics Letters, 1993, 62, 3452-3454.	3.3	20
131	Electron capture time measurements in GaAs/AlGaAs quantumâ€well infrared photodetectors: Photoresponse saturation by a freeâ€electron laser. Journal of Applied Physics, 1995, 78, 1224-1229.	2.5	20
132	Harvesting, Coupling, and Control of Single-Exciton Coherences in Photonic Waveguide Antennas. Physical Review Letters, 2016, 116, 163903.	7.8	20
133	Femtosecond-luminescence study of electron transfer in type-II GaAs/AlAs superlattices: Intervalley scattering versus state mixing. Physical Review B, 1994, 49, 13560-13563.	3.2	19
134	Efficient coupling of Er-doped silicon-rich oxide to microdisk whispering gallery modes. Applied Physics Letters, 2005, 86, 111117.	3.3	19
135	Resonant excitation of intraband absorption in InAs/GaAs self-assembled quantum dots. Journal of Applied Physics, 1998, 84, 4356-4362.	2.5	18
136	Far-field radiation from quantum boxes located in pillar microcavities. Optics Letters, 2001, 26, 1595.	3.3	18
137	Towards a single-mode single photon source based on single quantum dots. Journal of Luminescence, 2001, 94-95, 797-803.	3.1	18
138	Electron and hole spin cooling efficiency in InAs quantum dots: The role of nuclear field. Applied Physics Letters, 2010, 96, .	3.3	18
139	Non-exponential spontaneous emission dynamics for emitters in a time-dependent optical cavity. Optics Express, 2013, 21, 23130.	3.4	18
140	Quantum optics with quantum dots. European Physical Journal D, 2014, 68, 1.	1.3	18
141	Midinfrared unipolar photoluminescence in InAs/GaAs self-assembled quantum dots. Physical Review B, 1999, 60, 15589-15592.	3.2	17
142	Dephasing of intersublevel polarizations in InAs/GaAs self-assembled quantum dots. Physical Review B, 2002, 66, .	3.2	17
143	Large and Uniform Optical Emission Shifts in Quantum Dots Strained along Their Growth Axis. Nano Letters, 2016, 16, 3215-3220.	9.1	17
144	Optical investigation of the band structure of InAs/GaAs shortâ€period superlattices. Applied Physics Letters, 1989, 55, 559-561.	3.3	16

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145	Quantum wires in multidimensional microcavities: Effects of photon dimensionality on emission properties. Physical Review B, 2002, 66, .	3.2	16
146	Single quantum dot spectroscopy of CdSe/ZnSe grown on vicinal GaAs substrates. Applied Physics Letters, 2003, 82, 2227-2229.	3.3	16
147	Control of the two-dimensional–three-dimensional transition of self-organized CdSe/ZnSe quantum dots. Nanotechnology, 2005, 16, 1116-1118.	2.6	16
148	Kerr and free carrier ultrafast all-optical switching of GaAs/AlAs nanostructures near the three photon edge of GaAs. Journal of Applied Physics, 2008, 104, .	2.5	16
149	Monitoring stimulated emission at the single-photon level in one-dimensional atoms. Physical Review A, 2012, 85, .	2.5	16
150	Differential ultrafast all-optical switching of the resonances of a micropillar cavity. Applied Physics Letters, 2014, 105, .	3.3	16
151	Design of polarization-insensitive superconducting single photon detectors with high-index dielectrics. Superconductor Science and Technology, 2017, 30, 035005.	3.5	16
152	Metal-organic vapor-phase epitaxy of defect-free InGaAs/GaAs quantum dots emitting around 1.3μm. Journal of Crystal Growth, 2002, 235, 89-94.	1.5	15
153	Relation between growth procedure and confinement properties ofCdSeâ^•ZnSequantum dots. Physical Review B, 2006, 74, .	3.2	15
154	Surface effects in a semiconductor photonic nanowire and spectral stability of an embedded single quantum dot. Applied Physics Letters, 2011, 99, .	3.3	15
155	Universal optimal broadband photon cloning and entanglement creation in one-dimensional atoms. Physical Review A, 2012, 86, .	2.5	15
156	Toward high-efficiency quantum-dot single-photon sources. , 2004, 5361, 88.		14
157	Polarization-insensitive fiber-coupled superconducting-nanowire single photon detector using a high-index dielectric capping layer. Optics Express, 2018, 26, 17697.	3.4	14
158	Photonic "hourglass―design for efficient quantum light emission. Optics Letters, 2019, 44, 2617.	3.3	14
159	Quantum-mechanical versus semiclassical capture and transport properties in quantum well laser structures. Optical and Quantum Electronics, 1994, 26, S679-S689.	3.3	13
160	Growth of InGaAs/GaAs heterostructures with abrupt interfaces on the monolayer scale. Journal of Crystal Growth, 1995, 150, 467-472.	1.5	13
161	Strong Purcell effect for InAs quantum boxes in high-Q wet-etched microdisks. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 641-645.	2.7	13
162	Static strain tuning of quantum dots embedded in a photonic wire. Applied Physics Letters, 2018, 112, .	3.3	13

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163	A nanowire optical nanocavity for broadband enhancement of spontaneous emission. Applied Physics Letters, 2021, 118, .	3.3	13
164	Disorder-induced photoluminescence up-conversion in InAs/GaAs quantum-dot samples. Journal of Applied Physics, 2002, 91, 5489-5491.	2.5	12
165	New method to induce 2D–3D transition of strained CdSe/ZnSe layers. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 119-123.	2.7	12
166	Observation of hot luminescence and slow inter-sub-band relaxation in Si-doped GaNâ^•AlxGa1â^'xN (x=0.11, 0.25) multi-quantum-well structures. Journal of Applied Physics, 2006, 99, 093513.	2.5	12
167	Competition between electronic Kerr and free-carrier effects in an ultimate-fast optically switched semiconductor microcavity. Journal of the Optical Society of America B: Optical Physics, 2012, 29, 2630.	2.1	12
168	Observation of a stronger-than-adiabatic change of light trapped in an ultrafast switched GaAs-AlAs microcavity. Journal of the Optical Society of America B: Optical Physics, 2012, 29, A1.	2.1	12
169	A novel high-efficiency single-mode single photon source. Annales De Physique, 2007, 32, 151-154.	0.2	12
170	Optical investigation of some statistic and kinetic aspects of the nucleation and growth of inas islands on gaas. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 37, 8-16.	3.5	11
171	Comment on "Single-Mode Spontaneous Emission from a Single Quantum Dot in a Three-Dimensional Microcavity― Physical Review Letters, 2003, 90, 229701; author reply 229702.	7.8	11
172	Optical properties of single non-polar GaN quantum dots. Physica Status Solidi (B): Basic Research, 2006, 243, 1652-1656.	1.5	11
173	High-quality NbN nanofilms on a GaN/AlN heterostructure. AIP Advances, 2014, 4, 107123.	1.3	11
174	Modulated molecular beam epitaxy: a successful route toward high quality highly strained heterostructures. Journal of Crystal Growth, 1991, 111, 205-209.	1.5	10
175	Fast photorefractive materials using quantum wells. Optical Materials, 1995, 4, 348-353.	3.6	10
176	InAs quantum boxes in GaAs/AlAs pillar microcavities: from spectroscopic investigations to spontaneous emission control. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 804-808.	2.7	10
177	How to avoid non-radiative escape of excitons from quantum dots?. Physica Status Solidi (B): Basic Research, 2004, 241, 542-545.	1.5	10
178	Giant nonlinear interaction between two optical beams via a quantum dot embedded in a photonic wire. Physical Review B, 2018, 97, .	3.2	10
179	Improvement of the critical temperature of NbTiN films on III-nitride substrates. Superconductor Science and Technology, 2019, 32, 035008.	3.5	10
180	Electron Phonon Interaction and Polaron Effects in Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 1941-1946.	1.5	9

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181	Pump–probe analysis of polaron decay in InAs/GaAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 59-62.	2.7	9
182	Design of Quantum Dot-Nanowire Single-Photon Sources that are Immune to Thermomechanical Decoherence. Physical Review Letters, 2019, 123, 247403.	7.8	9
183	Plasmons in the modulated and confined 2DEG: A Raman scattering study. Superlattices and Microstructures, 1994, 15, 441-445.	3.1	8
184	Self-organized growth of quantum boxes. Applied Surface Science, 1996, 92, 526-531.	6.1	8
185	Glancing-angle diffraction anomalous fine structure of InAs quantum dots and quantum wires. Journal of Synchrotron Radiation, 2001, 8, 536-538.	2.4	8
186	Glancing angle EXAFS of encapsulated self-assembled InAs/InP quantum wires and InAs/GaAs quantum dots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 174-180.	3.5	8
187	Boosting photon storage. Nature Materials, 2003, 2, 140-141.	27.5	8
188	Electric-Field Sensing with a Scanning Fiber-Coupled Quantum Dot. Physical Review Applied, 2017, 8, .	3.8	8
189	Prospects of High-Efficiency Quantum Boxes Obtained by Direct Epitaxial Growth. NATO ASI Series Series B: Physics, 1995, , 357-381.	0.2	8
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